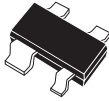




BAW101

DUAL, ISOLATED HIGH VOLTAGE SWITCHING DIODES



SOT-143 CASE

# Central<sup>TM</sup> Semiconductor Corp.

## DESCRIPTION

The CENTRAL SEMICONDUCTOR BAW101 type is a Silicon Dual Isolated High Voltage Switching diode designed for surface mount switching applications requiring high voltage capabilities.

**Marking Code is CJP.**

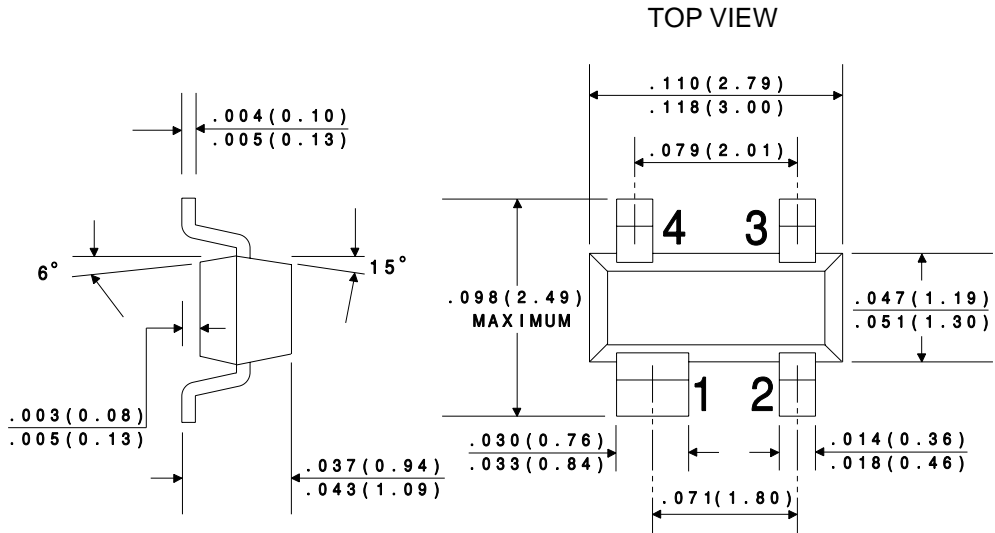
## MAXIMUM RATINGS (T<sub>A</sub>=25°C)

	SYMBOL		UNITS
Continuous Reverse Voltage	V <sub>R</sub>	300	V
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	300	V
Continuous Forward Current	I <sub>F</sub>	200	mA
Peak Repetitive Forward Current	I <sub>FRM</sub>	500	mA
Forward Surge Current, tp=1 μs	I <sub>FSM</sub>	4500	mA
Power Dissipation	P <sub>D</sub>	350	mW
Operating and Storage			
Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	Θ <sub>JA</sub>	357	°C/W

## ELECTRICAL CHARACTERISTICS PER DIODE (T<sub>A</sub>=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>R</sub>	V <sub>R</sub> =250V			150	nA
I <sub>R</sub>	V <sub>R</sub> =250V, T <sub>A</sub> =150°C			50	μA
B <sub>V</sub> R	I <sub>R</sub> =100μA	300			V
V <sub>F</sub>	I <sub>F</sub> =100mA		0.9	1.3	V
C <sub>T</sub>	V <sub>R</sub> =0V, f=1.0MHz			5.0	pF
t <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =30mA, I <sub>rr</sub> =3.0mA, R <sub>L</sub> =100Ω			50	ns

All Dimensions in Inches (mm).



LEAD CODE:

- 1) Cathode 1
- 2) Cathode 2
- 3) Anode 2
- 4) Anode 1